# SRDA3.3-4 RailClamp® Low Capacitance TVS Array

# PROTECTION PRODUCTS - RailClamp®

### Description

RailClamps are surge rated diode arrays designed to protect high speed data interfaces. The SRDA series has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by electrostatic discharge (ESD), electrical fast transients (EFT), and lightning.

The unique design incorporates surge rated, low capacitance steering diodes and a TVS diode in a single package. During transient conditions, the steering diodes direct the transient current to ground via the internal low voltage TVS. The TVS diode clamps the transient voltage to a safe level. The low capacitance array configuration allows the user to protect up to four high-speed data lines.

The SRDA3.3-4 is constructed using Semtech's proprietary EPD process technology. The EPD process provides low stand-off voltages with significant reductions in leakage current and capacitance over siliconavalanche diode processes. They feature a true operating voltage of 3.3 volts for superior protection.

These devices are in a 8-pin SOIC package. It measures 3.9 x 4.9mm. They are available with a SnPb or RoHS/WEEE compliant matte tin lead finish. The high surge capability (Ipp=25A, tp=8/20 $\mu$ s) means it can be used in high threat environments in applications such as CO/CPE equipment, telecommunication lines, and video lines.

#### **Features**

- ◆ Transient protection for high-speed data lines to IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact) IEC 61000-4-4 (EFT) 40A (5/50ns) IEC 61000-4-5 (Lightning) 24A (8/20µs)
- Array of surge rated diodes with internal TVS diode
- Protects four I/O lines
- ◆ Low capacitance (<15pF) for high-speed interfaces
- Low operating voltage: 3.3V
- Low clamping voltage
- Solid-state technology

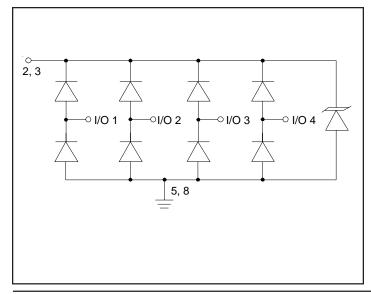
## Mechanical Characteristics

- ◆ JEDEC SOIC-8 package
- ◆ Lead Finish: SnPb or Matte Sn
- Molding compound flammability rating: UL 94V-0
- Marking: Part number, date code, logo
- ◆ Packaging: Tape and Reel per EIA 481

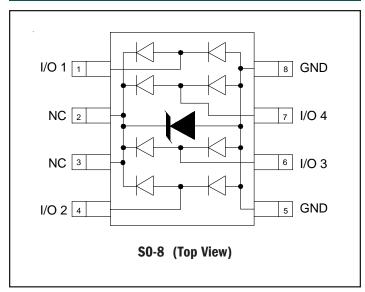
### **Applications**

- ◆ T1/E1 secondary IC Side Protection
- ◆ T3/E3 secondary IC Side Protection
- Analog Video Protection
- Microcontroller Input Protection
- Base stations
- ◆ I<sup>2</sup>C Bus Protection

## Circuit Diagram



# Schematic and PIN Configuration





# Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p = 8/20\mu s$ )	P <sub>pk</sub>	500	Watts
Peak Pulse Current ( $t_p = 8/20\mu s$ )	I <sub>PP</sub>	25	А
Lead Soldering Temperature	T <sub>L</sub>	260 (10 sec.)	°C
Operating Temperature	T <sub>J</sub>	-40 to +85	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

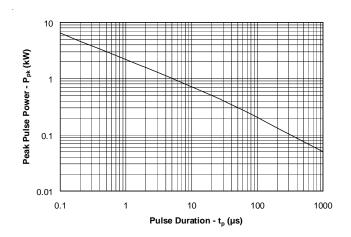
# Electrical Characteristics (T=25°C)

SRDA3.3-4						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V <sub>RWM</sub>				3.3	V
Punch-Through Voltage	V <sub>PT</sub>	Ι <sub>ΡΤ</sub> = 2μΑ	3.5			V
Snap-Back Voltage	V <sub>SB</sub>	I <sub>SB</sub> = 50mA	2.8			V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 3.3V, T=25°C			1	μΑ
Clamping Voltage	V <sub>c</sub>	$I_{pp} = 1A, t_p = 8/20 \mu s$			5.3	V
Clamping Voltage	V <sub>c</sub>	$I_{pp} = 10A, t_{p} = 8/20\mu s$			10	V
Clamping Voltage	V <sub>c</sub>	$I_{pp} = 25A, t_{p} = 8/20\mu s$			15	V
Junction Capacitance	C <sub>j</sub>	Between I/O pins and Ground V <sub>R</sub> = OV, f = 1MHz		8	15	pF
		Between I/O pins V <sub>R</sub> = OV, f = 1MHz		4		pF

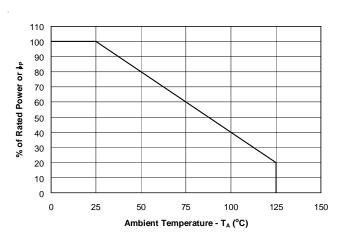


# Typical Characteristics

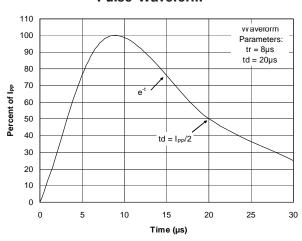
### Non-Repetitive Peak Pulse Power vs. Pulse Time



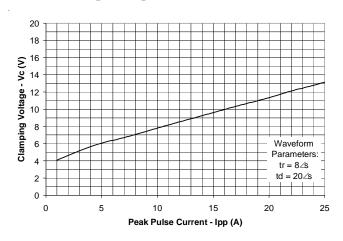
### **Power Derating Curve**



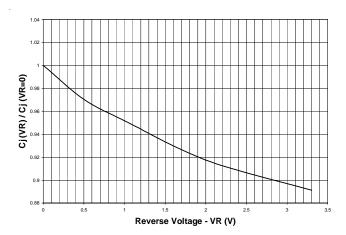
### **Pulse Waveform**



## Clamping Voltage vs. Peak Pulse Current



# Normalized Junction Capacitance vs. Reverse Voltage





### **Applications Information**

# **Device Connection Options for Protection of Four High-Speed Data Lines**

These devices are designed to protect low voltage data lines operating at 3.3 volts. When the voltage on the protected line exceeds the punch-through or "turn-on" voltage of the TVS diode, the steering diodes are forward biased, conducting the transient current away from the sensitive circuitry.

Data lines are connected at pins 1, 4, 6 and 7. Pins 5 and 8 should be connected directly to a ground plane. The path length is kept as short as possible to minimize parasitic inductance.

Note that pins 2 and 3 are connected internally to the cathode of the low voltage TVS. It is not recommended that these pins be directly connected to a DC source greater than the snap-back votlage ( $V_{SB}$ ) as the device can latch on as described below.

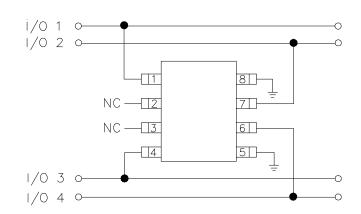
### **EPD TVS Characteristics**

These devices are constructed using Semtech's proprietary EPD technology. By utilizing the EPD technology, the SRDA3.3-4 can effectively operate at 3.3V while maintaining excellent electrical characteristics.

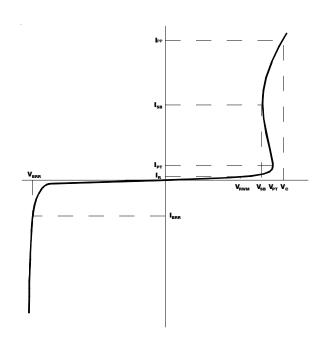
The EPD TVS employs a complex nppn structure in contrast to the pn structure normally found in traditional silicon-avalanche TVS diodes. Since the EPD TVS devices use a 4-layer structure, they exhibit a slightly different IV characteristic curve when compared to conventional devices. During normal operation, the device represents a high-impedance to the circuit up to the device working voltage  $(V_{RWM})$ . During an ESD event, the device will begin to conduct and will enter a low impedance state when the punch through voltage  $(V_{pT})$  is exceeded. Unlike a conventional device, the low voltage TVS will exhibit a slight negative resistance characteristic as it conducts current. This characteristic aids in lowering the clamping voltage of the device, but must be considered in applications where DC voltages are present.

When the TVS is conducting current, it will exhibit a slight "snap-back" or negative resistance characteristics due to its structure. This point is defined on the curve by the snap-back voltage ( $V_{\rm SB}$ ) and snap-back

# Data Line Protection Using Internal TVS Diode as Reference



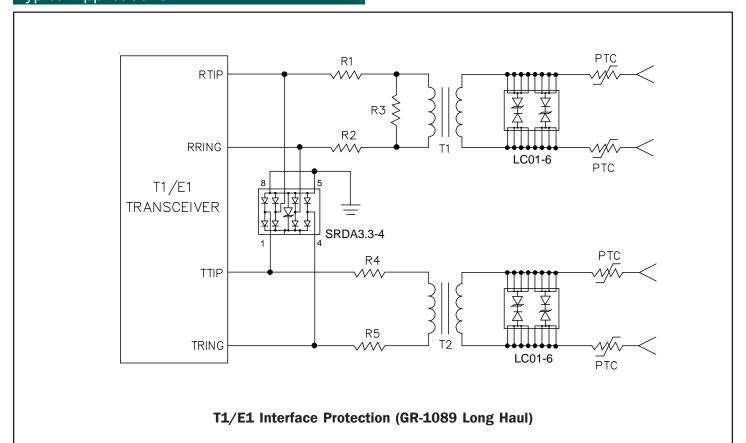
**EPD TVS IV Characteristic Curve** 



current ( $I_{SB}$ ). To return to a non-conducting state, the current through the device must fall below the  $I_{SB}$  (approximately <50mA) and the voltage must fall below the  $V_{SB}$  (normally 2.8 volts for a 3.3V device). If a 3.3V TVS is connected to 3.3V DC source, it will never fall below the snap-back voltage of 2.8V and will therefore stay in a conducting state.

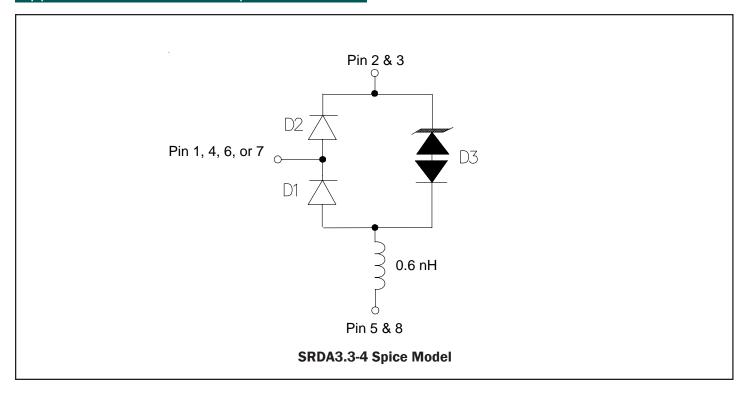


# Typical Applications





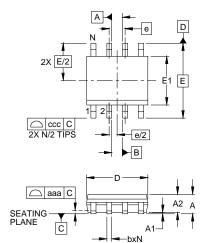
# Applications Information - Spice Model

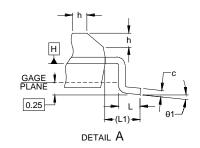


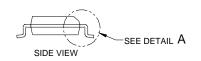
SRDA3.3-4 Spice Parameters								
Parameter	Unit	D1 (LCRD)	D2 (LCRD)	D3 (TVS)				
IS	Amp	2.092E-11	2.156E-12	6.09E-14				
BV	Volt	680	240	3.54				
VJ	Volt	0.62	0.64	13.8				
RS	Ohm	0.180	0.155	0.220				
IBV	Amp	1E-3	1E-3	10E-3				
CJO	Farad	5.2E-12	6.2E-12	45E-12				
TT	sec	2.541E-9	2.541E-9	2.541E-9				
М		0.058	0.058	0.111				
N		1.1	1.1	1.1				
EG	eV	1.11	1.11	1.11				



# Outline Drawing - SO-8







DIMENSIONS							
DIM	INCHES			MILLIMETERS			
ווווטן	MIN	NOM	MAX	MIN	NOM	MAX	
Α	.053	-	.069	1.35	-	1.75	
A1	.004	-	.010	0.10	-	0.25	
A2	.049	-	.065	1.25	-	1.65	
b	.012	-	.020	0.31	-	0.51	
С	.007	-	.010	0.17	-	0.25	
D	.189 .193		.197	4.80	4.90	5.00	
E1	.150 .154		.157	3.80	3.90	4.00	
Е	.2	236 BS	С	6	.00 BS	С	
е	.(	050 BS	С	1	.27 BS	С	
h	.010	-	.020	0.25	-	0.50	
L	.016	.028	.041	0.40	0.72	1.04	
L1		(.041)		(1.04)			
N	8			8			
θ1	0° -		8°	0°	-	8°	
aaa	.004			0.10			
bbb	.010			0.25			
CCC	.008				0.20		

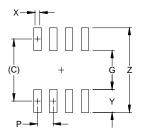
#### NOTES:

1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).

⊕ bbb∭ C A-B D

- 2. DATUMS -A- AND -B- TO BE DETERMINED AT DATUM PLANE -H-
- 3. DIMENSIONS "E1" AND "D" DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- 4. REFERENCE JEDEC STD MS-012, VARIATION AA.

# Land Pattern - SO-8



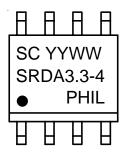
DIMENSIONS							
DIM	INCHES	MILLIMETERS					
С	(.205)	(5.20)					
G	.118	3.00					
Р	.050	1.27					
Х	.024	0.60					
Υ	.087	2.20					
Z	.291	7.40					

#### NOTES:

- THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY.
  CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR
  COMPANY'S MANUFACTURING GUIDELINES ARE MET.
- 2. REFERENCE IPC-SM-782A, RLP NO. 300A.



# Marking Diagram



# **Ordering Information**

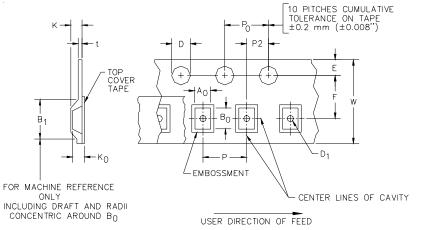
Part Number	Lead Finish	Qty per Reel	Reel Size
SRDA3.3-4.TB SnPb		500	7 Inch
SRDA3.3-4.TBT Matte Sn		500	7 Inch

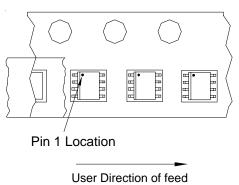
Note: Lead-free devices are RoHS/WEEE Compliant

Note:

YYWW = Date Code

# Tape and Reel Specification





### **Device Orientation in Tape**

A0	ВО	ко
6.50 +/-0.20 mm	5.40 +/-0.20 mm	2.00 +/-0.10 mm

Tape Width	B, (Max)	D	D1	E	F	K (MAX)	Р	PO	P2	T(MAX)	W
12 mm	8.2 mm	1.5 + 0.1 mm - 0.0 mm	1.5 mm	1.750±.10 mm	5.5±0.05 mm	4.5 mm	4.0±0.1 mm	4.0±0.1 mm	2.0±0.05 mm	0.4 mm	12.0 mm ±0.3

# Contact Information

Semtech Corporation Protection Products Division 200 Flynn Road, Camarillo, CA 93012 Phone: (805)498-2111 FAX (805)498-3804